

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Original) A semiconductor device having a plurality of MOSFETs where a source region, a drain region and a channel forming region are formed in a semiconductor substrate, respectively,

wherein impurity regions of a conductive type opposite to that of said source region and said drain region are disposed locally in a channel width direction on a junction portion of said drain region within said channel forming region.

2-38 (Canceled)